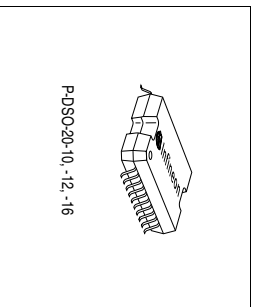


Preliminary Datasheet

1 Overview

1.1 Features

- Operating supply voltage 5 V to 28 V
- Typical $R_{DSon} = 150\text{ m}\Omega$ for each output transistor (at 25 °C)
- Continuous DC load current 3.5 A ($T_C < 100\text{ }^\circ\text{C}$)
- Output current limitation at typ. 6.6 A \pm 1.1 A
- Short circuit shut down for output currents over 8 A
- Logic- inputs TTL/CMOS-compatible
- Operating-frequency up to 30 kHz
- Over temperature protection
- Short circuit protection
- Undervoltage disable function
- Diagnostic by SPI or Status-Flag (configurable)
- Enable and Disable input
- P-DSO-20-12 power package



| Type | Ordering Code | Package |
|-----------|---------------|-------------|
| TLE 7209R | on request | P-DSO-20-12 |

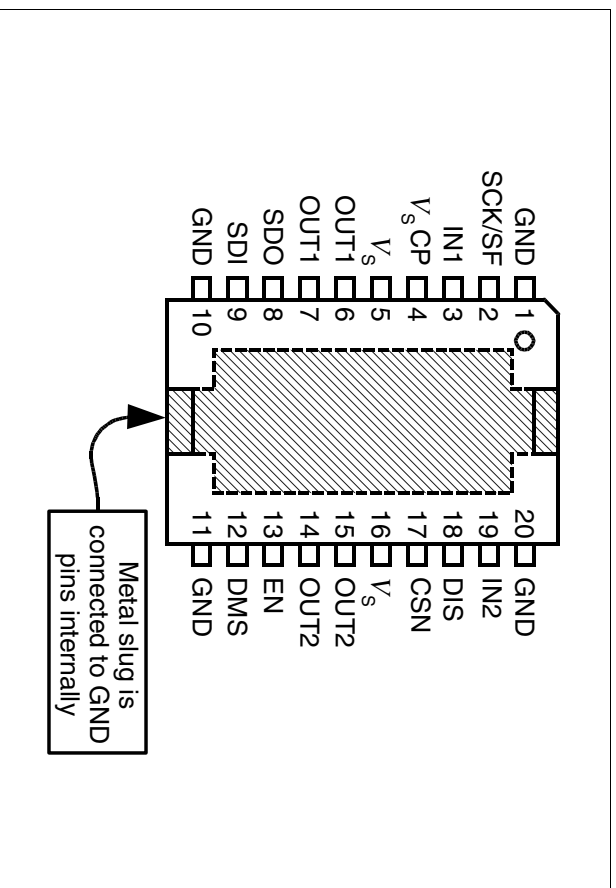
Functional Description

The TLE 7209R is an intelligent full H-Bridge, designed for the control of DC and stepper motors in safety critical applications and under extreme environmental conditions.

The H-Bridge is protected against over temperature and short circuits and has an under voltage lockout for all the supply voltages "V_S" (main DC power supply). All malfunctions cause the output stages to go tristate.

The device is configurable by the DMS pin. When grounded, the device gives diagnostic information via a simple error flag. When supplied with V_{CC} = 5 V, the device works in SPI mode. In this mode, detailed failure diagnosis is available via the serial interface.

1.2 Pin Configuration



Pin Definitions and Functions

| Pin. No. | Symbol | Function |
|----------|------------------|--|
| 1 | GND | Ground |
| 2 | SCK/SF | SPI-Clock/Status-flag |
| 3 | IN1 | Input 1 |
| 4 | V _{SCP} | Supply voltage for internal charge pump |
| 5 | V _S | Supply voltage |
| 6 | OUT1 | Output 1 |
| 7 | OUT1 | Output 1 |
| 8 | SDO | Serial data out |
| 9 | SDI | Serial data in |
| 10 | GND | Ground |
| 11 | GND | Ground |
| 12 | DMS | Diagnostic-Mode selection (+ Supply voltage for SPI-Interface) |
| 13 | EN | Enable |
| 14 | OUT2 | Output 2 |
| 15 | OUT2 | Output 2 |
| 16 | V _S | Supply voltage; must be connected to pin 5 |
| 17 | CSN | Chip Select (low active) |
| 18 | DIS | Disable |
| 19 | IN2 | Input 2 |
| 20 | GND | Ground |

Table 1 Pinning

1.3 Block Diagram

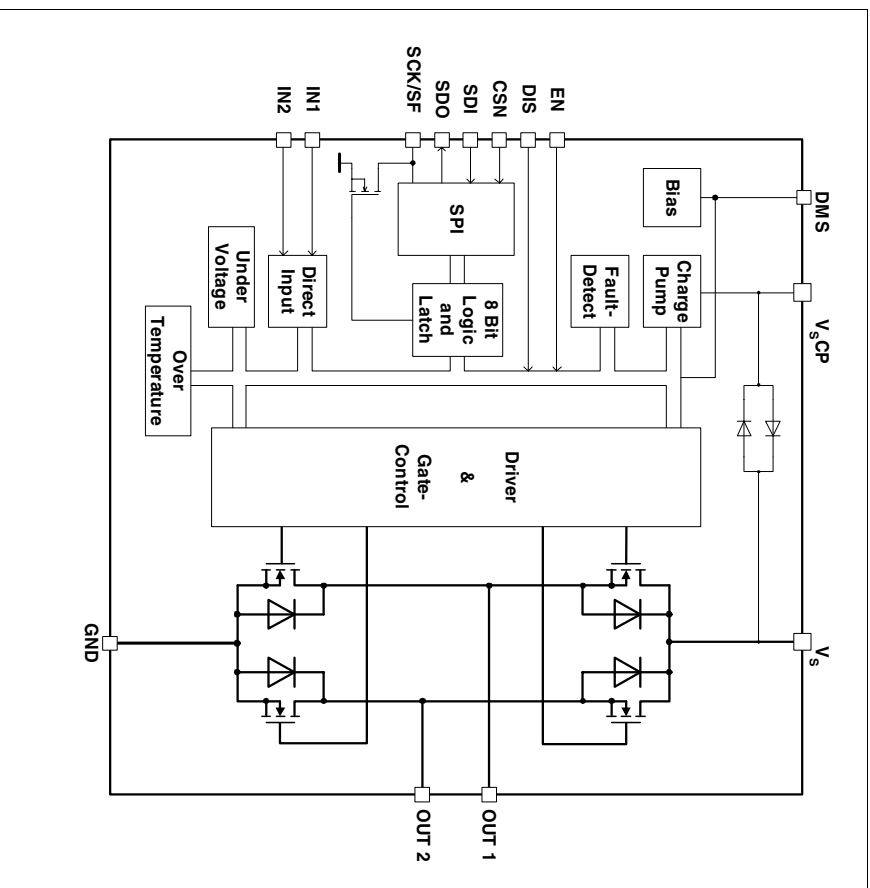


Figure 2 Block Diagram TLE 7209R

2 Circuit Description

2.1 Control Inputs

The bridge is controlled by the Inputs IN1, IN2, DIS and EN as shown in **Table 2**. The outputs OUT1 and OUT2 are set to High or Low by the parallel inputs IN1 and IN2, respectively. In addition, the outputs can be disabled (set to tristate) by the Disable and Enable inputs DIS and EN.

Inputs IN1, IN2 and DIS have an internal pull-up. Input EN has an internal pull-down.

Functional Truth Table

| Pos. | DIS | EN | IN1 | IN2 | OUT1 | OUT2 | SF ¹⁾ | SP1 ²⁾ DIA_REG |
|---------------------------|-----|----|-----|-----|------|------|------------------|------------------------------|
| 1. Forward | L | H | H | L | H | L | H | see Chapter 2.4.2 |
| 2. Reverse | L | H | L | H | L | H | H | |
| 3. Free-wheeling low | L | H | L | L | L | L | H | |
| 4. Free-wheeling high | L | H | H | H | H | H | H | |
| 5. Disable | H | X | X | X | Z | Z | L | |
| 6. Enable | X | L | X | X | Z | Z | L | |
| 7. IN1 disconnected | L | H | Z | X | H | X | H | |
| 8. IN2 disconnected | L | H | X | Z | X | H | H | |
| 9. DIS disconnected | Z | X | X | X | Z | Z | L | |
| 10. EN disconnected | X | Z | X | X | Z | Z | L | |
| 11. Current limit. active | L | H | X | X | Z | Z | H | |
| 12. Under Voltage | X | X | X | X | Z | Z | L | |
| 13. Over temperature | X | X | X | X | Z | Z | L | |
| 14. Over current | X | X | X | X | Z | Z | L | |

¹⁾ If Mode "Status-Flag" is selected (see **Chapter 2.4**)

²⁾ If Mode "SP1-Diagnosis" is selected (see **Chapter 2.4**)

Table 2 Functional Truth Table

2.2 Power Stages

Four n-channel power-DMOS transistors build up the output H-bridge. Integrated circuits protect the outputs against over current and over temperature if there is a short-circuit to ground, to the supply voltage or across the load. Positive and negative voltage spikes, which occur when switching inductive loads, are limited by integrated freewheeling diodes. To drive the gates of the high-side DMOS, an internal charge pump is integrated to generate a voltage higher than the supply voltage.

2.2.1 Chopper Current Limitation

To limit the output current at low power loss, a chopper current limitation is integrated as shown in **Figure 3**. The current is measured by sense cells integrated in the low-side switches. As soon the current limit I_L is reached, the low-side switch is switched off for a fixed time t_a .

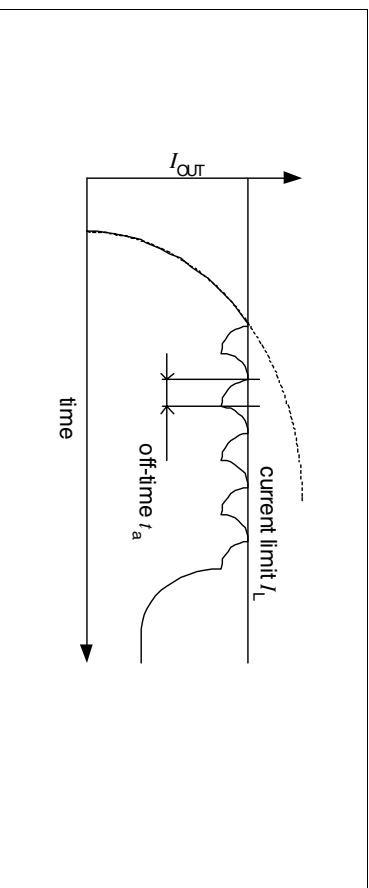


Figure 3 Chopper current limitation

2.2.2 Temperature-dependent Current Limitation

For $165\text{ }^{\circ}\text{C} < T_J < 175\text{ }^{\circ}\text{C}$ the current limit decreases from $I_L = 6.6\text{ A} \pm 1.1\text{ A}$ to $I_L = 2.5\text{ A} \pm 1.1\text{ A}$ as shown in Figure 4

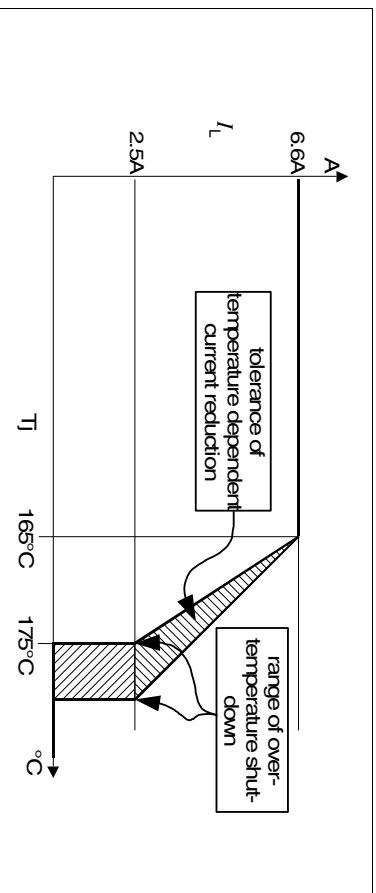


Figure 4 Temperature dependent current limitation

2.3 Protection

The TLE 7209R is protected against short circuits, overload and invalid supply Voltage by the following measures:

2.3.1 Short circuit to Ground

The high-side switches are protected against a short of the output to ground by an over current shutdown. If a high-side switch is turned on and the current rises above the short circuit detection current I_{OUC} all output transistors are turned off and the error bit "Short Circuit to Ground on output 1 (2)", SCG1 (SCG2) is stored in the internal status register.

2.3.2 Short circuit to V_S

Due to the chopper current regulation, the low-side switches are already protected against a short to the supply voltage. To be able to distinguish a short circuit from normal current limit operation, the current limitation is deactivated for the blanking time t_b after the current has exceeded the current limit threshold I_L . If the short circuit detection current I_{OUC} is reached within this blanking time, a short circuit is detected (see Figure 5). All output transistors are turned OFF and the according error bit "Short Circuit to Battery on output 1 (2)", SCB1 (SCB2) is set.

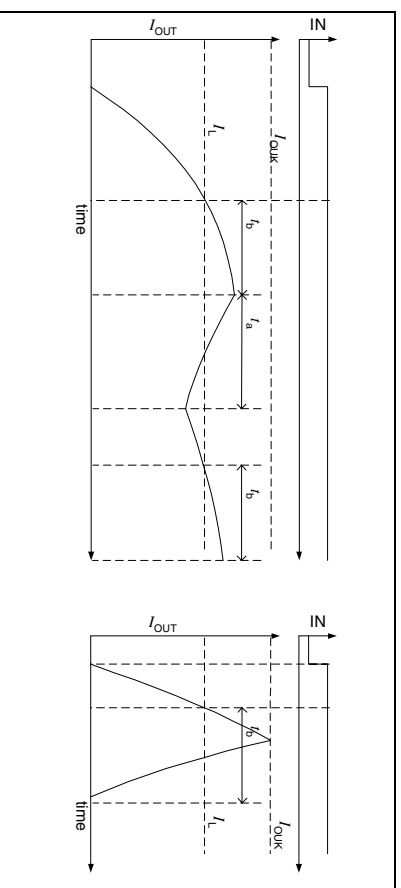


Figure 5 Short to V_S detection. Left: normal operation. Right: short circuit is detected

2.3.3 Short circuit across the load

If short circuit messages from high- and low-side switch occur simultaneously within a delay time of typically 2 μs , the error bit "Short Circuit Over Load", SCOL is set.

2.4.2.2 Characteristics of the SPI Interface

1. When DMS is > 3.5V, the SPI is active, independently of the state of EN or DIS. During active reset conditions (DMS < 3.5V) the SPI is driven into its default state. When reset becomes inactive, the state machine enters into a wait-state for the next instruction.
2. If the slave select signal at CSN is inactive (high), the state machine is forced to enter the wait-state, i.e. the state machine waits for the following instruction.
3. During active (low) state of the select signal CSN the falling edge of the serial clock signal SCK will be used to latch the input data at SDI. Output data at SDO are driven with the rising edge of SCK (see timing diagram **Figure 13**)
4. Chip-address:

In order to establish the option of extended addressing the uppermost two bits of the instruction-byte (i.e. the first two SDI-bits of a Frame) are reserved to send a chip-address. To avoid a bus conflict the output SDO must stay high impedant during the addressing phase of a frame (i.e. until the address-bits are recognized as valid chip-address), if the chip-address does not match, the data at SDI will be ignored and SDO remains high impedant for the complete frame. See also **Figure 7**
5. Verification byte:

Simultaneously to the receipt of an SPI instruction TLE 7209R transmits a check byte via the output SDO to the controller. This byte indicates normal or abnormal operation of the SPI. It contains an initial bit pattern and a flag indicating an invalid instruction of the previous access.
6. Because only read access is used in the TLE 7209R, the SDI data-bits (2nd byte) are not used
7. Invalid instruction/access:

An instruction is invalid, if an unused instruction code is detected (see tables with SPI instructions). In case an unused instruction code occurred, the data byte "ff_{hex}" (no error) will be transmitted after having sent the verification byte. This transmission takes place within the same SPI-frame that contained the unused instruction byte. In addition any transmission is invalid if the number of SPI clock pulses (falling edge) counted during active CSN differs from exactly 16 clock pulses. If an invalid instruction is detected, bit TRANS_F in the following verification byte (next SPI transmission) is set to HIGH. The TRANS_F bit must not be cleared before it has been sent to the micro controller.

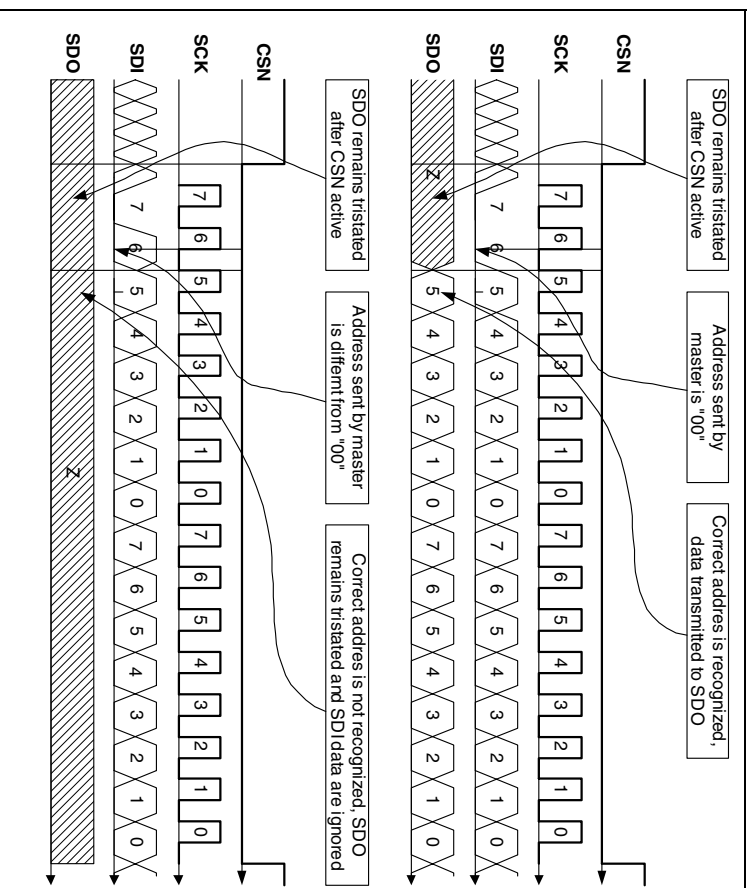
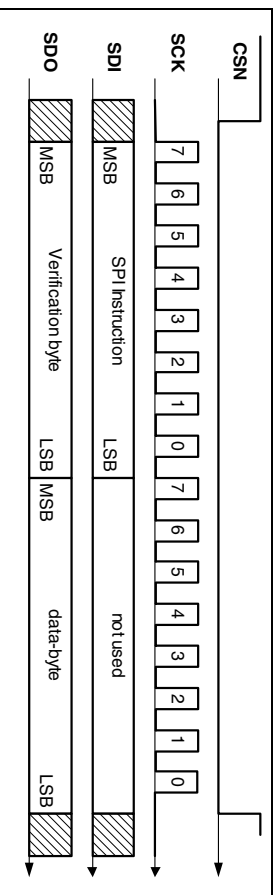


Figure 7 bus-arbitration by chip-address

2.4.2.3 SPI-Communication

The 16 input bits consist of the SPI-instruction byte and a second, unused byte. The 16 output bits consist of the verification-byte and the data-byte (see also **Figure 8**). The definition of these bytes is given in the subsequent sections.


Figure 8 SPI communication
2.4.2.4 SPI instruction

The uppermost 2 bit of the instruction byte contain the chip-address. The chip-address of the TLE 7209R is 00. During read-access, the output data according to the register requested in the instruction byte are applied to SDO within the same SPI frame. That means, the output data corresponding to an instruction byte sent during one SPI frame are transmitted to SDO during the same SPI frame.

Table 3 SPI Instruction Format

| MSB | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-----|---|---------|---------|---------|---------|--------|-------|---|
| 0 | 0 | INST R4 | INST R3 | INST R2 | INST R1 | INS R0 | INS W | |

Table 4 SPI instruction Description

| Bit | Name | Description |
|-----|--------------|-----------------------------------|
| 7,6 | CPAD1,0 | Chip Address (has to be '0', '0') |
| 5-1 | INST R (4-0) | SPI instruction (encoding) |
| 0 | INS W | Even parity |

Table 5 SPI Instruction-Bytes Encoding

| SPI Instruction | Encoding | | Description |
|-----------------|--------------------|------------------------|--|
| | bit 7,6 CPAD1,0 | bit 5-1 INST R(4-0) | |
| RD_IDENT | 00 | 00000 | 0 read identifier |
| RD_VERSION | 00 | 00001 | 1 read version |
| RD_DIA | 00 | 00100 | 1 read DIA_REG |
| - | 00 | all others | X unused, TRANS_F is set to high, ff_hex is sent as data bit |
| - | all others | xxxxx | X invalid address, SDO remains tristate during entire SPI frame |

2.4.2.5 Verification Byte
Table 6 Verification Byte Format

| MSB | 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-----|---|---|---|---|---|---|---|---------|
| Z | Z | Z | 1 | 0 | 1 | 0 | 1 | TRANS_F |

Table 7 Verification Byte Description

| Bit | Name | Description |
|-----|---------|--|
| 0 | TRANS_F | Bit = 1: error detected during previous transfer Bit = 0: previous transfer was recognized as valid |
| 1 | | Fixed to High |
| 2 | | Fixed to Low |
| 3 | | Fixed to High |
| 4 | | Fixed to Low |
| 5 | | Fixed to High |
| 6 | | send as high impedance |
| 7 | | send as high impedance |

The default value after power-up at DMS of the TRANS_F bit is L (previous transfer valid)

2.4.2.6 Data-byte: Diagnostics/Encoding of Failures (Register DIA_REG, SPI Instruction RD_DIA)
Table 8 DIA_REG Format

| MSB | | | | | | | |
|--------|----|---------|---------|-------|-------|-------|-------|
| 7 | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
| EN/DIS | OT | CurrRed | CurrLim | DIA21 | DIA20 | DIA11 | DIA10 |

Table 9 DIA_REG Description

 Default value after reset is FF_{hex}. Access by controller is read only

| Bit | Name | Description | latch behavior |
|-----|---------|---|----------------|
| 0 | DIA 10 | Diagnosis-Bit1 of OUT1 | see below |
| 1 | DIA 11 | Diagnosis-Bit2 of OUT1 | see below |
| 2 | DIA 20 | Diagnosis-Bit1 of OUT2 | see below |
| 3 | DIA 21 | Diagnosis-Bit2 of OUT2 | see below |
| 4 | CurrLim | is set to „0“ in case of current limitation. | latched |
| 5 | CurrRed | is set to „0“ in case of temperature dependent current limitation | latched |
| 6 | OT | is set to „0“ in case of over temperature | latched |
| 7 | EN/DIS | is set to „0“ in case of EN = L or DIS = H | not latched |

| EN | DIS | DIA_REG_7 |
|----|-----|-----------|
| H | L | 1 |
| L | L | 0 |
| H | H | 0 |
| L | H | 0 |

Table 10 Encoding of the Diagnostic Bits of OUT1 and OUT2

| DIA21 | DIA20 | DIA 11 | DIA10 | Description | latch behavior |
|-------|-------|--------|-------|---|----------------|
| 1 | 1 | 0 | 0 | Short circuit over load (SCOL) | latched |
| - | - | 0 | 1 | Short circuit to battery on OUT1 (SCB1) | latched |
| - | - | 1 | 0 | Short circuit to ground on OUT1 (SCG1) | latched |
| - | - | 1 | 1 | No error detected on OUT1 | - |
| 0 | 0 | 1 | 1 | Open load (OL) | latched |
| 0 | 1 | - | - | Short circuit to battery on OUT2 (SCB2) | latched |
| 1 | 0 | - | - | Short circuit to ground on OUT2 (SCG2) | latched |
| 1 | 1 | - | - | No error detected on OUT2 | - |
| 0 | 0 | 0 | 0 | Under Voltage on Pin Vs | not latched |

Failure Encoding in case of multiple faults

If multiple faults are stored in the failure register, the faults that are encoded in the DIAxx bits can not be displayed simultaneously due to the encoding scheme that is used. In this case, errors are encoded according to the following priority list.

- Priority 1: Under Voltage (please note that after removal of Under Voltage, the original error will be restored, see below)
- Priority 2: Short circuit across the load
- Priority 3: all other short circuits
- Priority 4: open load

If a failure of higher priority is detected, the failures of lower priority are no longer visible in the encoded SPI message

Fault storage and reset of the Diagnosis Register DIA_REG

On the following conditions DIA_REG is reset:

- With the rising edge of the CSN-Signal after the SPI-Instruction RD_DIA. This reset only takes place if the correct number of 16 CLK pulses has been counted.
- When the voltage on DMS exceeds the threshold for detecting SPI-Mode (after under Voltage condition).

Under Voltage on Vs (< 5.0V) sets Bit 0... Bit 3 of DIA_REG to 0000. If Vs rises over the under Voltage level, the Bits of DIA_REG are restored (when DMS > 3.5V).

A rising edge on EN or a falling edge on DIS re-activates the output power-stages, but does not reset the DIA_REG register.

2.4.2.7 Data-byte: Device Identifier and Version (SPI Instructions RD_IDENT and RD_VERSION)

The IC's identifier (device ID) and version number are used for production test purposes and features plug & play functionality depending on the systems software release. The two numbers are read-only accessible via the SPI instructions RD_IDENT and RD_VERSION as described in **Section 2.4.2.4**.

The device ID is defined to allow identification of different IC-Types by software and is fixed for the TLE 7209R.

The Version number may be utilized to distinguish different states of hardware and is updated with each redesign of the TLE 7209R. The contents is divided into an upper 4 bit field reserved to define revisions (SWR) corresponding to specific software releases and a lower 4 bit field utilized to identify the actual mask set revision (MSR).

Both (SWR and MSR) will start with 0000b and are increased by 1 every time an according modification of the hardware is introduced.

Reading the IC Identifier (SPI Instruction: RD_IDENT):

Table 11 Device Identifier Format

| MSB | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|-----|-----|-----|-----|-----|-----|-----|-----|
| ID7 | ID6 | ID5 | ID4 | ID3 | ID2 | ID1 | ID0 |

Table 12 Device Identifier Description

| Bit | Name | Description |
|-------|------------------|------------------|
| 7...0 | device-ID(7...0) | ID-No.: 10100010 |

Reading the IC version number (SPI Instruction: RD_VERSION):

Table 13 IC version number Format

| MSB | 6 | 5 | 4 | 3 | 2 | 1 | 0 |
|------|------|------|------|------|------|------|------|
| SWR3 | SWR2 | SWR1 | SWR0 | MSR3 | MSR2 | MSR1 | MSR0 |

Table 14 IC version number Description

| Bit | Name | Description |
|-------|------------|-----------------------------------|
| 7...4 | SWR(3...0) | This register is set to 0 |
| 3...0 | MSR(3...0) | Version corresponding to Mask set |

2.4.2.8 Open-Load Diagnosis

Open-load diagnostic in OFF-state is possible in the SPI-mode (DMS = 5 V) if the device is Disabled (EN = L or DIS = H). The detection mechanism is explained in **Figure 9**. The according diagnostic information can be read out via the SPI diagnostic register. The resulting overall diagnostic truth-table is shown as **Table 15**

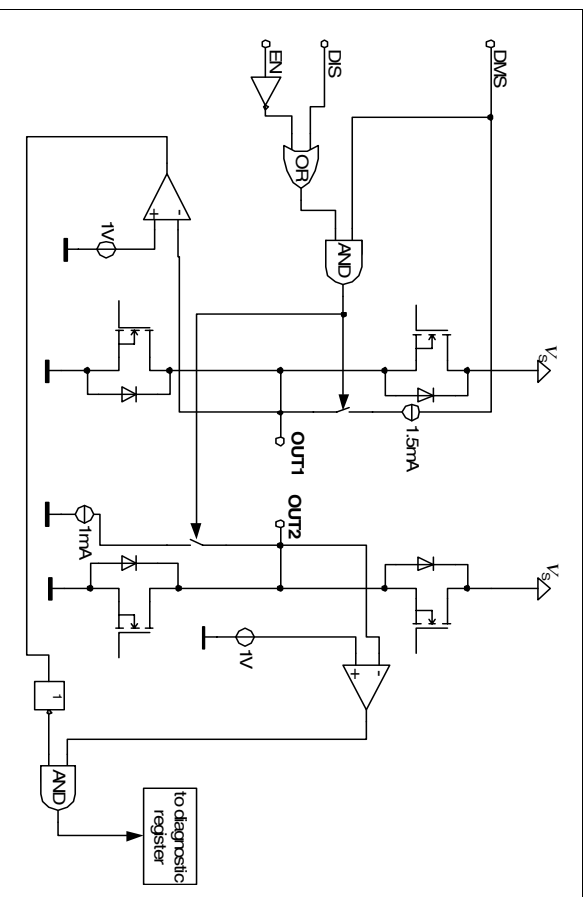


Figure 9 Functional block diagram of open-load detection

Table 15 Diagnosis Truth Table for open load detection

| Output stage inactive, EN = low or DIS = high, DMS > 4.5 V | OUT1 | OUT2 | |
|--|------|------|--------------------------------|
| Load available | H | H | |
| Open Load | H | L | OL detected |
| SC -> GND on OUT1 and Open Load | L | L | OL not detected – double Fault |
| SC -> GND on OUT2 and Open Load | H | L | OL detected |
| SC -> V _S on OUT1 and Open Load | H | L | OL detected |
| SC -> V _S on OUT2 and Open Load | H | H | OL not detected – double Fault |

3 Electrical Characteristics

3.1 Absolute Maximum Ratings

| Pos. | Parameter | Sym-bol | Limit Values | | Unit | Test Conditions |
|--------|---|---------------|--------------|-----------------|------|---|
| | | | min. | max. | | |
| 3.1.1 | Junction temperature | T_j | -40 | +150 | °C | – |
| | | | – | +175 | °C | dynamic: $t < 1$ s |
| 3.1.2 | Storage temperature | T_s | -55 | +125 | °C | – |
| 3.1.3 | Ambient temperature | T_a | -40 | +125 | °C | – |
| 3.1.4 | Supply voltage | V_S | -1 | 40 | V | static destruction proof |
| | | | -2 | 40 | V | dynamic destruction proof $t < 0.5$ s (single pulse, $T_j < 85$ °C) |
| 3.1.5 | Voltage at logic inputs IN1, IN2, DIS, EN, SDI, SCK/SF, DMS | V | -0.5 | 7 | V | – |
| 3.1.6 | Voltage at logic input CSN | V | -0.5 | 40 | V | – |
| 3.1.7 | Voltage at logic output SDO | V | -0.5 | $V_{DMS} + 0.5$ | V | – |
| 3.1.8 | Voltage at SF in status-flag-mode | V_{SF} | -0.5 | 7 | V | $R \geq 10$ k Ω |
| 3.1.9 | Voltage at V _{sCP} | V_{Gp} | $V_S - 0.5$ | $V_S + 0.5$ | V | – |
| 3.1.10 | ESD voltage human body model (MIL STD 883D / ANSI EOS/ESD S5.1) | V_{ESD} | – | – | 2kV | all pins |
| 3.1.11 | | $V_{ESD-out}$ | – | – | 8kV | only pins 6, 7, 14 and 15 (outputs) |

Note: Maximum ratings are absolute ratings; exceeding any one of these values may cause irreversible damage to the integrated circuit.

Electrical Characteristics
3.2 Operating Range

| Pos. | Parameter | Sym-bol | Limit Values | | Unit | Remark |
|-------|----------------------|------------------|--------------|------|------|---|
| | | | min. | max. | | |
| 3.2.1 | Supply Voltage | V _S | 5 | 28 | V | |
| 3.2.2 | DMS Supply Voltage | V _{DMS} | 4.5 | 5.5 | V | Device in SPI-mode |
| 3.2.3 | PWM frequency | f | – | 30 | KHz | May be limited to lower values in the application due to switching losses |
| 3.2.4 | Junction Temperature | T _J | -40 | 150 | °C | |

Note: In the operating range, the circuit functionality as described in the circuit description is fulfilled.

3.3 Thermal Resistance

| | | | | | | |
|-------|------------------|-------------------|---|-----|-----|-------------------|
| 3.3.1 | Junction-case | R _{thJC} | – | 1.5 | K/W | – |
| 3.3.2 | Junction-ambient | R _{thJA} | – | 50 | K/W | minimal footprint |

Electrical Characteristics
3.4 Electrical Characteristics

5V < V_S < 28V; – 40 °C < T_J < 150 °C; unless otherwise specified

| Pos. | Parameter | Symbol | Limit Values | | | Unit | Test Conditions |
|------|-----------|--------|--------------|------|------|------|-----------------|
| | | | min. | typ. | max. | | |

Power Supply

| | | | | | | | |
|-------|---------------------------------|---------------------|---|-----|----|----|------------------------------------|
| 3.4.1 | Under voltage at V _S | V _{UV OFF} | – | 4.7 | 5 | V | |
| 3.4.2 | Supply current | I _{UB} | – | – | 30 | mA | f = 20 KHz, I _{OUT} = 0 A |
| | | | – | – | 20 | mA | f = 0 Hz, I _{OUT} = 0 A |

Logic Inputs IN1, IN2, DIS, EN

| | | | | | | | |
|-------|-------------------------------|------------------|------|------|-----|----|---------|
| 3.4.3 | Input "high" | V _{IH} | 2 | – | – | V | – |
| 3.4.4 | Input "low" | V _{IL} | – | – | 1 | V | – |
| 3.4.5 | Input hysteresis | V _{IHY} | 0.1 | – | 0.6 | V | – |
| 3.4.6 | pull-up current IN1, IN2, DIS | I _{IL} | –200 | –125 | – | µA | U ≤ 1 V |
| 3.4.7 | pull-down current EN | I _{IH} | – | – | 100 | µA | U ≥ 2 V |

Power Outputs OUT1, OUT2

| | | | | | | | |
|-------|----------------------|---|---|---|-----|----|--|
| 3.4.8 | Switch on resistance | – | – | – | 300 | mΩ | R _{OUT-UB} , R _{OUT-GND} V _S > 5 V |
|-------|----------------------|---|---|---|-----|----|--|

Current limitation: Peak value controlled, load L = 0.8 ... 5 mH in series with R = 0.8 ... 1.8 Ω

| | | | | | | | |
|--------|--|------------------|-----|------|-----|----|---|
| 3.4.9 | Switch-off current | I _L | 5.5 | 6.6 | 7.7 | A | –40 °C < T _J < 165 °C |
| | | | – | 2.5 | – | A | T _J < 175 °C |
| 3.4.10 | Switch-off time | t _a | 8 | 14 | 22 | µs | – |
| 3.4.11 | Blanking time | t _b | 8 | 11.5 | 15 | µs | – |
| 3.4.12 | Short circuit detection current | I _{OUK} | 8 | – | 20 | A | – |
| 3.4.13 | Reactivation time after internal shut down | t | – | – | 200 | µs | Overcurrent- or overtemperature shut down to reactivation of the output stage |

Note: Reactivation time is guaranteed by design

| | | | | | | | |
|--------|-----------------|---|---|---|-----|----|---------------------------|
| 3.4.14 | Leakage current | – | – | – | 200 | µA | Output stage switched off |
|--------|-----------------|---|---|---|-----|----|---------------------------|

Electrical Characteristics
3.4 Electrical Characteristics (cont'd)

 5V < V_S < 28V; -40 °C < T_J < 150 °C; unless otherwise specified

| Pos. | Parameter | Symbol | Limit Values | | | Unit | Test Conditions |
|--------|--|----------|--------------|------|------|------|------------------------|
| | | | min. | typ. | max. | | |
| 3.4.15 | Free-wheel diode forward voltage | U_D | – | – | 2 | V | $I_{OUT} = 3\text{ A}$ |
| 3.4.16 | Free-wheel diode reverse recovery time | t_{rr} | – | – | 100 | ns | – |

Note: reverse recovery time is guaranteed by design
Output Status-flag, Open Drain Output DMS < 0.8 V

| | | | | | | | |
|--------|----------------------------|----------|-----|---|----|---------------|-------------------------|
| 3.4.17 | Output "high" (SF not set) | I_{SF} | – | – | 20 | μA | $V_{SF} = 5\text{ V}$ |
| 3.4.18 | Output "low" (SF set) | I_{SF} | 300 | – | – | μA | $V_{SF} = 1\text{ V}$ |
| | | | 100 | – | – | μA | $V_{SF} = 0.5\text{ V}$ |

Timing

| | | | | | | | |
|--------|--------------------------------|------------|---|---|---|---------------|---|
| 3.4.19 | Output ON-delay | t_{don} | – | 2 | 5 | μs | IN1 --> OUT1 resp. IN2 --> OUT2 |
| 3.4.20 | Output OFF-delay | t_{doff} | – | 2 | 5 | μs | IN1 --> OUT1 resp. IN2 --> OUT2 |
| 3.4.21 | Output switching time | t_r, t_f | – | 3 | 5 | μs | OUT1H --> OUT1L, OUT2H --> OUT2L, $I_{OUT} = 3\text{ A}$ OUT1L --> OUT1H, OUT2L --> OUT2H |
| 3.4.22 | Disable delay time | t_{dis} | – | – | 2 | μs | DIS --> OUT _n , EN --> OUT _n |
| 3.4.23 | Power on delay time | – | – | – | 1 | ms | $V_S = \text{on}$ --> output stage active |
| 3.4.24 | Delay time for fault detection | t_{df} | – | 2 | – | μs | – |

Electrical Characteristics
3.4 Electrical Characteristics (cont'd)

 5V < V_S < 28V; -40 °C < T_J < 150 °C; unless otherwise specified

| Pos. | Parameter | Symbol | Limit Values | | | Unit | Test Conditions |
|--------------------------------------|----------------|------------------|--------------|------|------|---------------|--|
| | | | min. | typ. | max. | | |
| Input SCK, SPI Clock Input | | | | | | | |
| 3.4.25 | Low Level | U_{SCKL} | – | – | 1 | V | – |
| 3.4.26 | High Level | U_{SCKH} | 2 | – | – | V | – |
| 3.4.27 | Hysteresis | ΔU_{SCK} | 0.1 | – | 0.4 | V | – |
| 3.4.28 | Input Capacity | C_{SCK} | – | – | 10 | pF | – |
| 3.4.29 | Input Current | $-I_{SCK}$ | – | 20 | 50 | μA | Pull-up current source connected to V_{DD} |
| Input CSN, Chip Select Signal | | | | | | | |
| 3.4.30 | Low Level | U_{CSNL} | – | – | 1 | V | TLE 7209R is selected |
| 3.4.31 | High Level | U_{CSNH} | 2 | – | – | V | – |
| 3.4.32 | Hysteresis | ΔU_{CSN} | 0.1 | – | 0.4 | V | – |
| 3.4.33 | Input Capacity | C_{CSN} | – | – | 10 | pF | – |
| 3.4.34 | Input Current | $-I_{CSN}$ | – | 20 | 50 | μA | Pull-up current source connected to V_{DD} |
| Input SDI, SPI Data Input | | | | | | | |
| 3.4.35 | Low Level | U_{SDIL} | – | – | 1 | V | – |
| 3.4.36 | High Level | U_{SDIH} | 2 | – | – | V | – |
| 3.4.37 | Hysteresis | ΔU_{SDI} | 0.1 | – | 0.4 | V | – |
| 3.4.38 | Input Capacity | C_{SDI} | – | – | 10 | pF | – |
| 3.4.39 | Input Current | $-I_{SDI}$ | – | 20 | 50 | μA | Pull up current source connected to V_{DD} |

Electrical Characteristics
3.4 Electrical Characteristics (cont'd)
 $5V < V_S < 28V; -40^\circ C < T_J < 150^\circ C$; unless otherwise specified

| Pos. | Parameter | Symbol | Limit Values | | | Unit | Test Conditions |
|------|-----------|--------|--------------|------|------|------|-----------------|
| | | | min. | typ. | max. | | |

Output SDO

Tristate Output of the TLE 7209R (SPI output):

| | | | | | | | |
|--------|-----------------|------------|------------------|---|-----|---------------|---------------------------------|
| 3.4.40 | Low Level | V_{SDOL} | – | – | 0.4 | V | $I_{SDO} = 2\text{ mA}$ |
| 3.4.41 | High Level | V_{SDOH} | $V_{DMS} - 0.75$ | – | – | V | $I_{SDO} = -2\text{ mA}$ |
| 3.4.42 | Capacity | C_{SDO} | – | – | 10 | pF | Capacity of the pin in tristate |
| 3.4.43 | Leakage Current | I_{SDO} | -10 | – | 10 | μA | In tristate |

Note: All in- and output pin capacities are guaranteed by design
Input DMS

Supply-Input for the SPI-Interface and Selection Pin for SPI- or SF-Mode

| | | | | | | | |
|--------|---------------|-----------|-----|---|-----|----|------------------|
| 3.4.44 | Input Voltage | V_{DMS} | 3.5 | – | – | V | SPI-Mode |
| | | V_{DMS} | – | – | 0.8 | V | Status-Flag-Mode |
| 3.4.45 | Input Current | I_{DMS} | – | – | 10 | mA | SPI-Mode |

Open-Load Diagnosis

| | | | | | | | |
|--------|------------------------------------|-------------|------|------|-------|---------------|--|
| 3.4.46 | Diagn. Threshold Load is available | V_{OUT1} | 0.8 | – | – | V | DMS > 4.5 V, EN < 0.8 V or DIS > 4.5 V |
| | | V_{OUT2} | 0.8 | – | – | V | |
| | | V_{OUT1} | 1 | – | V_S | V | Load is missing |
| 3.4.47 | Diagn. Current | I_{OUT2} | 700 | 1000 | 1400 | μA | DMS > 4.5 V, EN < 0.8 V or DIS > 4.5 V |
| | | $-I_{OUT1}$ | 1000 | 1500 | 2000 | μA | |
| 3.4.48 | Tracking Diag. C | – | 1.2 | 1.5 | 1.7 | – | I_{OUT1}/I_{OUT2} |
| 3.4.49 | Delay Time | t_p | 30 | – | 100 | ms | – |

Electrical Characteristics
3.4 Electrical Characteristics (cont'd)
 $5V < V_S < 28V; -40^\circ C < T_J < 150^\circ C$; unless otherwise specified

| Pos. | Parameter | Symbol | Limit Values | | | Unit | Test Conditions |
|------|-----------|--------|--------------|------|------|------|-----------------|
| | | | min. | typ. | max. | | |

SPI Timing (see Figure 13)

| | | | | | | | |
|--------|--|-----------------|------|---|-----|---------------|--|
| 3.4.50 | Cycle-Time (1) | t_{cyc} (1) | 200 | – | – | ns | referred to master |
| 3.4.51 | Enable Lead Time | t_{lead} (2) | 100 | – | – | ns | referred to master |
| 3.4.52 | Enable Lag Time | t_{lag} (3) | 150 | – | – | ns | referred to master |
| 3.4.53 | Data Valid | t_v (4) | – | – | 40 | ns | $C_L = 40\text{ pF}$ $C_T = 200\text{ pF}$ referred to TLE 7209R |
| 3.4.54 | Data Setup Time | t_{su} (5) | 50 | – | – | ns | referred to master |
| 3.4.55 | Data Hold Time | t_h (6) | 20 | – | – | ns | referred to master |
| 3.4.56 | Disable Time | t_{dis} (7) | – | – | 100 | ns | referred to TLE 7209R |
| 3.4.57 | Transfer Delay | t_{dt} (8) | 150 | – | – | ns | referred to master |
| 3.4.58 | Select time | t_{sckh} (9) | 50 | – | – | ns | referred to master |
| 3.4.59 | Access time | t_{sckl} (10) | 8.35 | – | – | μs | referred to master |
| 3.4.60 | Clock inactive before chips elect becomes valid | (11) | 200 | – | – | ns | – |
| 3.4.61 | Clock inactive after chips elect becomes invalid | (12) | 200 | – | – | ns | – |

Temperature Thresholds

| | | | | | | | |
|--------|----------------------------------|-----------|-----|---|---|------------------|--|
| 3.4.62 | Start of current limit reduction | T_{ILR} | 150 | – | – | $^\circ\text{C}$ | |
| 3.4.63 | Thermal Shutdown | T_{SD} | 175 | – | – | $^\circ\text{C}$ | |

Note: Temperature thresholds are guaranteed by design

4 Timing Diagrams

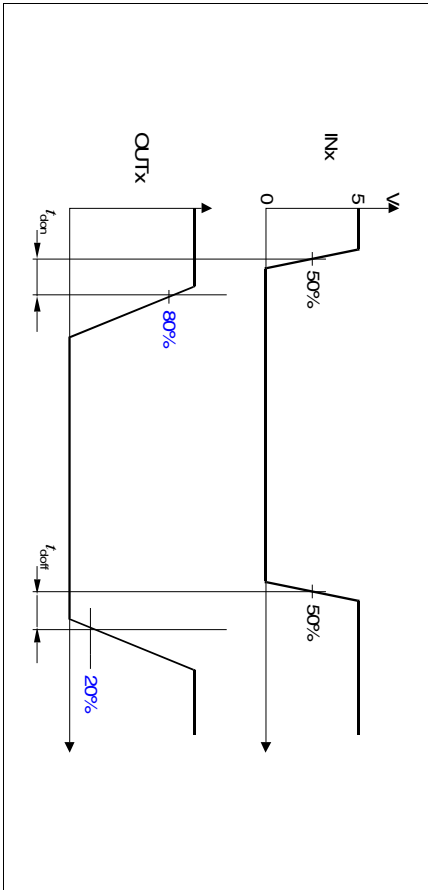


Figure 10 Output Delay Time

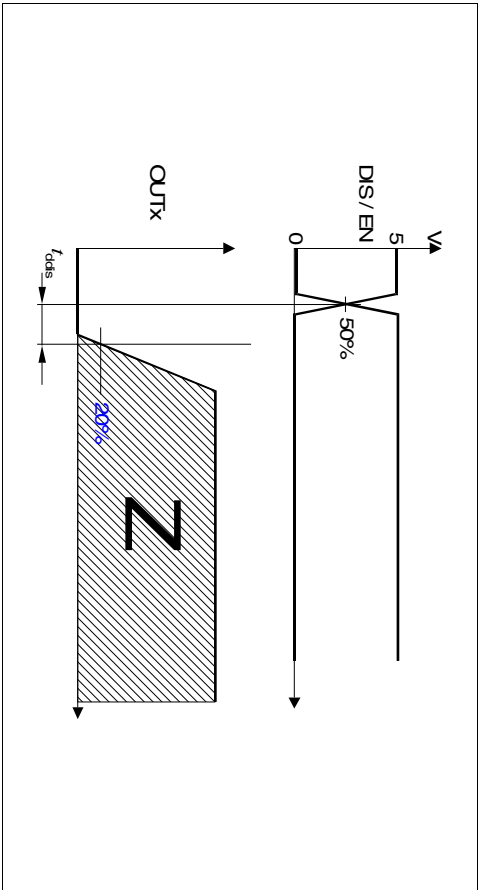


Figure 11 Disable Delay Time

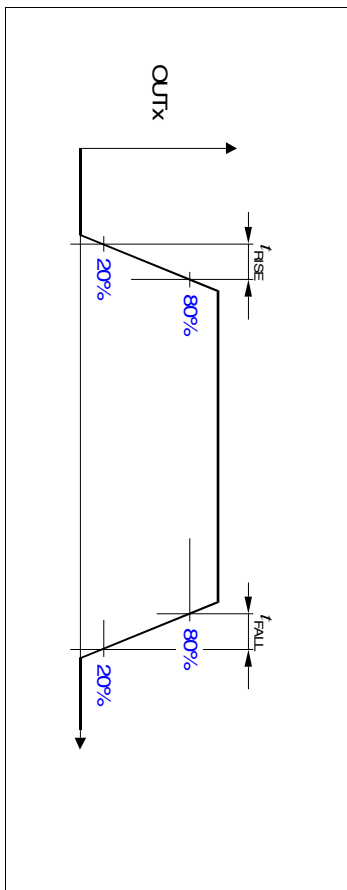


Figure 12 Output Switching Time

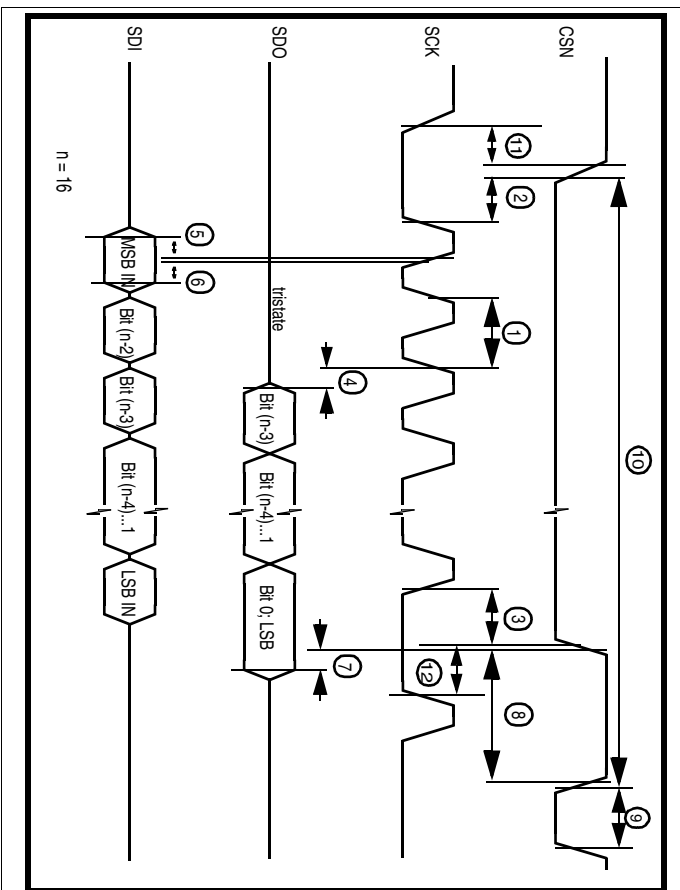


Figure 13 SPI-timing

5 Application

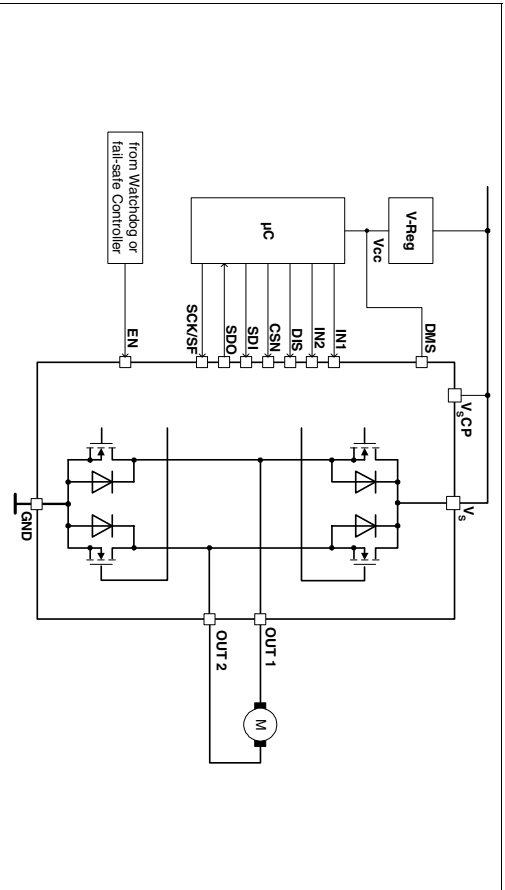


Figure 14 Application Example with SPI-Interface

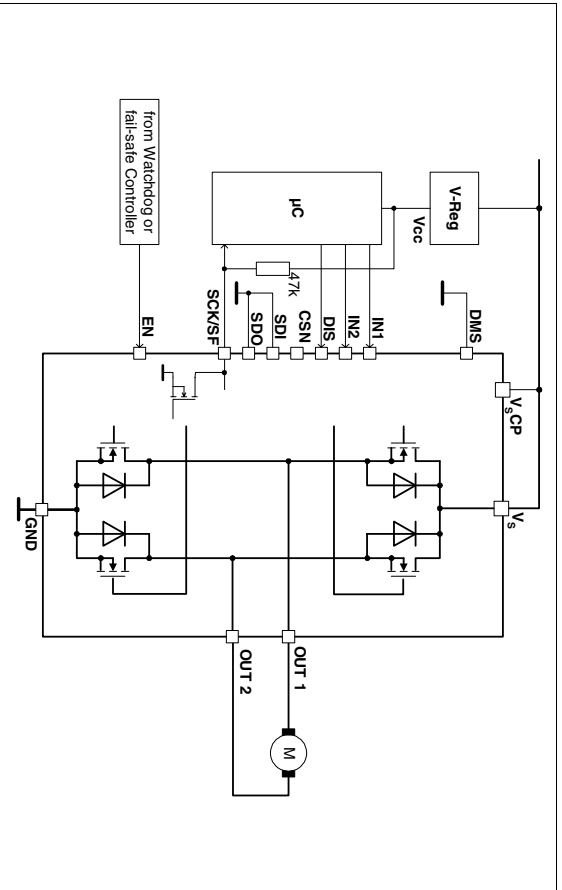


Figure 15 Application Example with Status-Flag

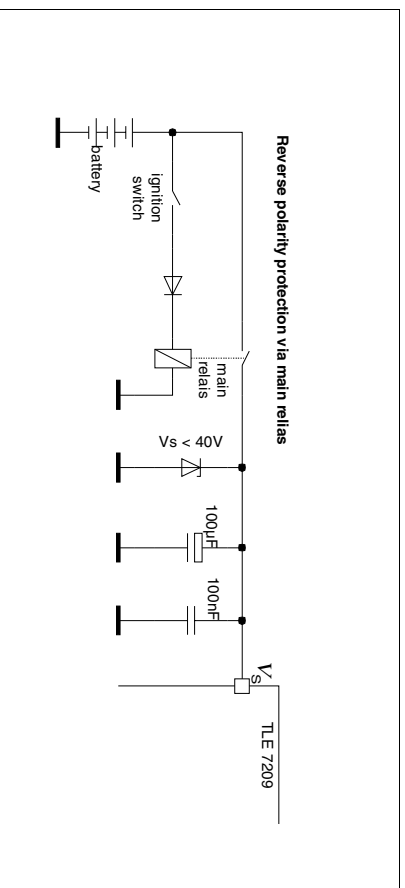
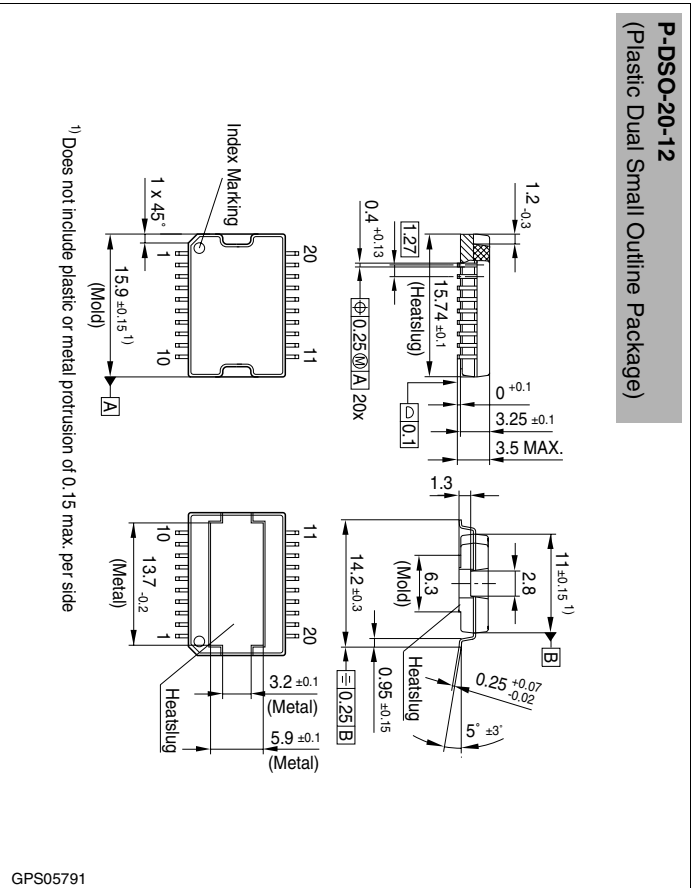


Figure 16 Application Examples for Over-Voltage- and Reverse-Voltage Protection

6 Package Outlines

P-DSO-20-12 (Plastic Dual Small Outline Package)



Sorts of Packing
Package outlines for tubes, trays etc. are contained in our Data Book "Package Information".

SMD = Surface Mounted Device

Dimensions in mm

Edition 2002-11-26
Published by Infineon Technologies AG,
St-Martin-Strasse 53,
D-81541 München, Germany
© Infineon Technologies AG 2002.
All Rights Reserved.

Attention please!

The information herein is given to describe certain components and shall not be considered as warranted characteristics.

Terms of delivery and rights to technical change reserved.

We hereby disclaim any and all warranties, including but not limited to warranties of non-infringement, regarding circuits, descriptions and charts stated herein.

Infineon Technologies is an approved CECC manufacturer.

Information

For further information on technology, delivery terms and conditions and prices please contact your nearest Infineon Technologies Office in Germany or our Infineon Technologies Representatives worldwide.

Warnings

Due to technical requirements components may contain dangerous substances. For information on the types in question please contact your nearest Infineon Technologies Office.

Infineon Technologies Components may only be used in life-support devices or systems with the express written approval of Infineon Technologies, if a failure of such components can reasonably be expected to cause the failure of that life-support device or system, or to affect the safety or effectiveness of that device or system. Life support devices or systems are intended to be implanted in the human body, or to support and/or maintain and sustain and/or protect human life. If they fail, it is reasonable to assume that the health of the user or other persons may be endangered.